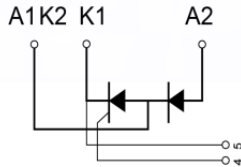


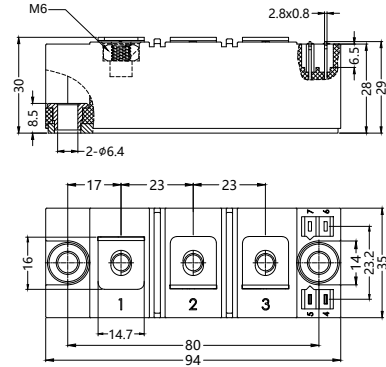
# STD130GKXXB

## Thyristor-Diode Modules



| Type        | $V_{RSM}$<br>$V_{DSM}$<br>V | $V_{RRM}$<br>$V_{DRM}$<br>V |
|-------------|-----------------------------|-----------------------------|
| STD130GK08B | 900                         | 800                         |
| STD130GK12B | 1300                        | 1200                        |
| STD130GK14B | 1500                        | 1400                        |
| STD130GK16B | 1700                        | 1600                        |
| STD130GK18B | 1900                        | 1800                        |

Dimensions in mm (1mm=0.0394")



| Symbol                                             | Test Conditions                                                                                                                                  | Maximum Ratings                            | Unit                 |
|----------------------------------------------------|--------------------------------------------------------------------------------------------------------------------------------------------------|--------------------------------------------|----------------------|
| $I_{TRMS}$ , $I_{FRMS}$<br>$I_{TAVM}$ , $I_{FAVM}$ | $T_V = T_{VJM}$<br>$T_C = 85^\circ\text{C}$ ; 180° sine                                                                                          | 300<br>130                                 | A                    |
| $I_{TSM}$ , $I_{FSM}$                              | $T_V = 45^\circ\text{C}$<br>$V_R = 0$<br>$t = 10\text{ms}$ (50Hz), sine<br>$t = 8.3\text{ms}$ (60Hz), sine                                       | 5500<br>5850                               | A                    |
|                                                    | $T_V = T_{VJM}$<br>$V_R = 0$<br>$t = 10\text{ms}$ (50Hz), sine<br>$t = 8.3\text{ms}$ (60Hz), sine                                                | 4800<br>5100                               |                      |
| $\int i^2 dt$                                      | $T_V = 45^\circ\text{C}$<br>$V_R = 0$<br>$t = 10\text{ms}$ (50Hz), sine<br>$t = 8.3\text{ms}$ (60Hz), sine                                       | 151000<br>142000                           | $\text{A}^2\text{s}$ |
|                                                    | $T_V = T_{VJM}$<br>$V_R = 0$<br>$t = 10\text{ms}$ (50Hz), sine<br>$t = 8.3\text{ms}$ (60Hz), sine                                                | 115000<br>108000                           |                      |
| $(di/dt)_{cr}$                                     | $T_V = T_{VJM}$<br>$f = 50\text{Hz}$ , $t_p = 200\mu\text{s}$<br>$V_D = 2/3 V_{DRM}$<br>$I_G = 0.5\text{A}$<br>$di/dt = 0.5\text{A}/\mu\text{s}$ | repetitive, $I_T = 500\text{A}$<br>150     | A/ $\mu\text{s}$     |
|                                                    |                                                                                                                                                  | non repetitive, $I_T = 500\text{A}$<br>500 |                      |
| $(dv/dt)_{cr}$                                     | $T_V = T_{VJM}$ ; $V_{DR} = 2/3 V_{DRM}$<br>$R_{GK} = \infty$ ; method 1 (linear voltage rise)                                                   | 1000                                       | V/ $\mu\text{s}$     |
| $P_{GM}$                                           | $T_V = T_{VJM}$<br>$I_T = I_{TAVM}$<br>$t_p = 30\mu\text{s}$<br>$t_p = 500\mu\text{s}$                                                           | 120<br>60                                  | W                    |
| $P_{GAV}$                                          |                                                                                                                                                  | 8                                          | W                    |
| $V_{RGM}$                                          |                                                                                                                                                  | 10                                         | V                    |
| $T_V$<br>$T_{VJM}$<br>$T_{stg}$                    |                                                                                                                                                  | -40...+125<br>125<br>-40...+125            | $^\circ\text{C}$     |
| $V_{ISOL}$                                         | 50/60Hz, RMS<br>$I_{ISOL} \leq 1\text{mA}$<br>$t = 1\text{min}$<br>$t = 1\text{s}$                                                               | 3000<br>3600                               | V~                   |
| $M_d$                                              | Mounting torque (M6)<br>Terminal connection torque (M6)                                                                                          | 2.25-2.75/20-25<br>4.5-5.5/40-48           | Nm/lb.in.            |
| Weight                                             | Typical                                                                                                                                          | 173                                        | g                    |

# STD130GKXXB

## Thyristor-Diode Modules

| Symbol             | Test Conditions                                                                                                | Characteristic Values | Unit             |
|--------------------|----------------------------------------------------------------------------------------------------------------|-----------------------|------------------|
| $I_{RRM}, I_{DRM}$ | $T_{VJ}=T_{VJM}; V_R=V_{RRM}; V_D=V_{DRM}$                                                                     | 10                    | mA               |
| $V_T, V_F$         | $I_T, I_F=390A; T_{VJ}=25^{\circ}C$                                                                            | 1.56                  | V                |
| $V_{TO}$           | For power-loss calculations only ( $T_{VJ}=125^{\circ}C$ )                                                     | 0.8                   | V                |
| $r_T$              |                                                                                                                | 1.5                   | mΩ               |
| $V_{GT}$           | $V_D=6V; T_{VJ}=25^{\circ}C$<br>$T_{VJ}=-40^{\circ}C$                                                          | 2.5<br>2.6            | V                |
| $I_{GT}$           | $V_D=6V; T_{VJ}=25^{\circ}C$<br>$T_{VJ}=-40^{\circ}C$                                                          | 150<br>200            | mA               |
| $V_{GD}$           | $T_{VJ}=T_{VJM}; V_D=2/3V_{DRM}$                                                                               | 0.2                   | V                |
| $I_{GD}$           |                                                                                                                | 10                    | mA               |
| $I_L$              | $T_{VJ}=25^{\circ}C; t_p=30\mu s; V_D=6V$<br>$I_G=0.5A; di_G/dt=0.5A/\mu s$                                    | 300                   | mA               |
| $I_H$              | $T_{VJ}=25^{\circ}C; V_D=6V; R_{GK}=\infty$                                                                    | 200                   | mA               |
| $t_{gd}$           | $T_{VJ}=25^{\circ}C; V_D=1/2V_{DRM}$<br>$I_G=0.5A; di_G/dt=0.5A/\mu s$                                         | 2                     | us               |
| $t_q$              | $T_{VJ}=T_{VJM}; I_T=160A; t_p=200\mu s; -di/dt=10A/\mu s$<br>$V_R=100V; dv/dt=20V/\mu s; V_D=2/3V_{DRM}$ typ. | 150                   | us               |
| $Q_s$              | $T_{VJ}=T_{VJM}; I_T, I_F=300A; -di/dt=50A/\mu s$                                                              | 550                   | uC               |
| $I_{RM}$           |                                                                                                                | 235                   | A                |
| $R_{thJC}$         | per thyristor/diode; DC current<br>per module                                                                  | 0.23<br>0.115         | K/W              |
| $R_{thJK}$         | per thyristor/diode; DC current<br>per module                                                                  | 0.33<br>0.165         | K/W              |
| $d_s$              | Creeping distance on surface                                                                                   | 12.7                  | mm               |
| $d_A$              | Strike distance through air                                                                                    | 9.6                   | mm               |
| $a$                | Maximum allowable acceleration                                                                                 | 50                    | m/s <sup>2</sup> |

### FEATURES

- \* International standard package
- \* Copper base plate
- \* Glass passivated chips
- \* Isolation voltage 3600 V~
- \* UL file NO.E310749
- \* RoHS compliant

### APPLICATIONS

- \* Motor control
- \* Power converter
- \* Heat and temperature control for industrial furnaces and chemical processes
- \* Lighting control
- \* Contactless switches

### ADVANTAGES

- \* Space and weight savings
- \* Simple mounting
- \* Improved temperature and power cycling
- \* Reduced protection circuits





# STD130GKXXB

## Thyristor-Diode Modules

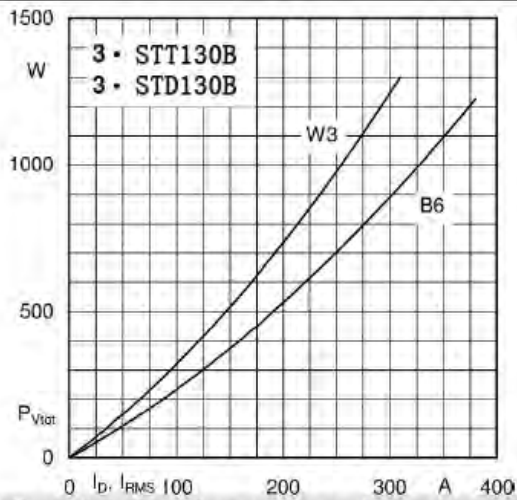


Fig. 4L Power dissipation of three modules vs. direct and rms current

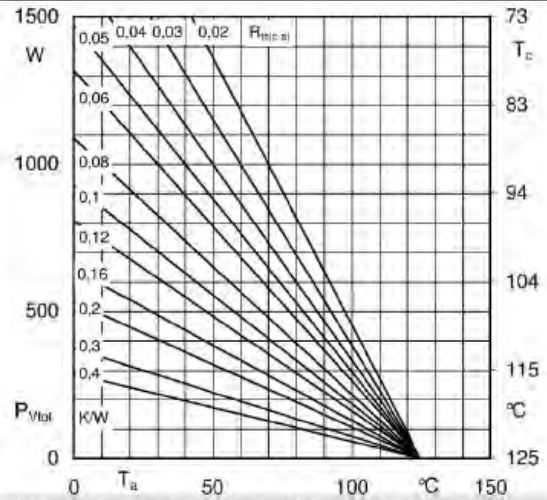


Fig. 4R Power dissipation of three modules vs. case temp.

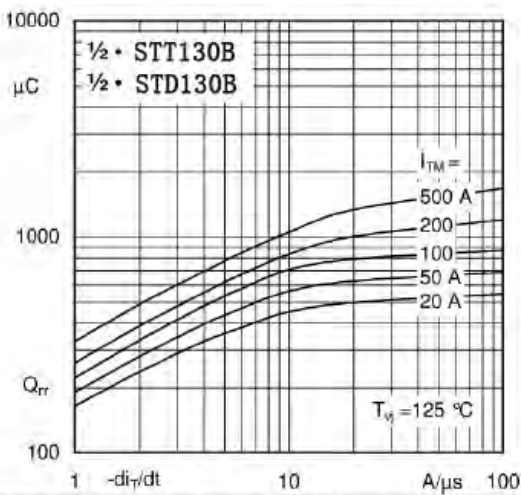


Fig. 5 Recovered charge vs. current decrease

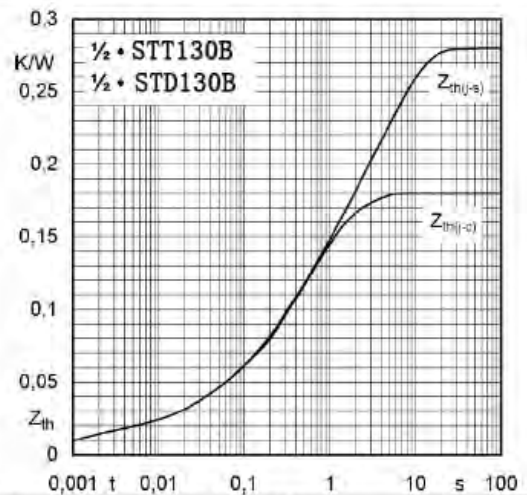


Fig. 6 Transient thermal impedance vs. time

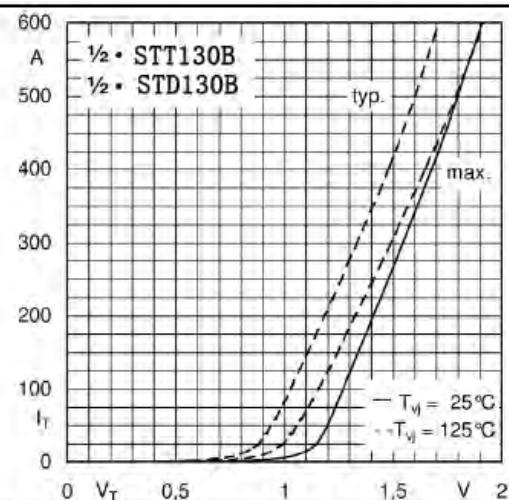


Fig. 7 On-state characteristics

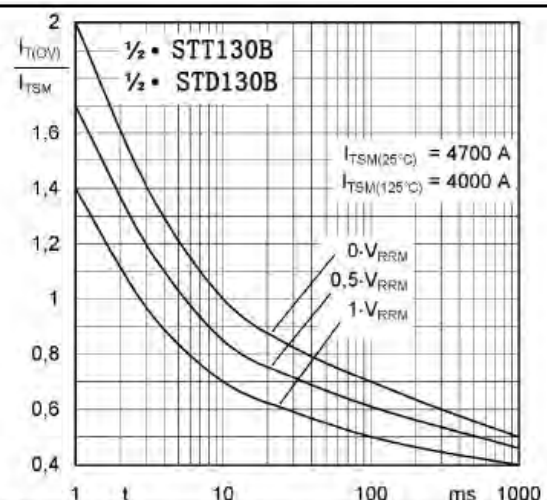


Fig. 8 Surge overload current vs. time